Sheet 1 of 1										
INFORMATION DISCLOSURE CITATION					Attorney Docket No.: 8017-1156		1	Application No	514	5
IN AN APPLICATION					Applicant: Akira USUI et al.					
(Use several sheets if necessary)					Filing Date: December 30, 2004			Group Art Unit:		
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EXAMINEB; / DATE CONSIDERED/										
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if										
not in conformance and not considered. Include copy of this form with next communication to the applicant.										

^{*} English language abstract provided for the Examiner's convenience